

## General Description

The WSD2018BDN22 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WSD2018BDN22 meet the RoHS and Green Product requirement with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

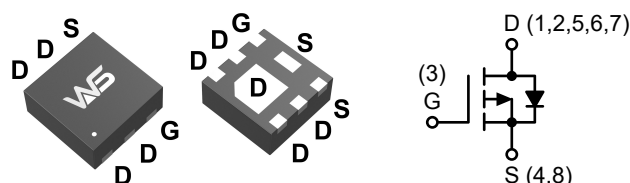
## Product Summary

$BV_{DSS}$	$R_{DS(on)}$	$I_D$
12V	8.6mΩ	12.3A

## Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## DFN2X2-6S Pin Configuration



## Absolute Maximum Ratings @ $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-Source Voltage	12	V
$V_{GSS}$	Gate-Source Voltage	$\pm 8$	V
$I_D$	Drain Current (Continuous) *C	$T_A=25^{\circ}\text{C}$	12.3
		$T_A=70^{\circ}\text{C}$	9.8
$I_{DM}$	Drain Current (Pulse) *B	49	A
$P_D$	Power Dissipation $T_A=25^{\circ}\text{C}$	2.8	W
$T_J/T_{STG}$	Operating Temperature/ Storage Temperature	-55~150	$^{\circ}\text{C}$

## Thermal Resistance Ratings

Symbol	Parameter	Maximum	Unit
$R_{thJA}$	Maximum Junction-to-Ambient *A	$t \leq 10\text{ s}$	45
			$^{\circ}\text{C/W}$

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static *D						
V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	12	---	---	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V	---	---	1	μA
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>DS</sub> = 250μA	0.4	0.6	1	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = ±8V, V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>DS(on)</sub>	Drain-Source On-state Resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8A	---	8.6	11.5	mΩ
R <sub>DS(on)</sub>		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4A	---	12	18	mΩ
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 1A , V <sub>GS</sub> =0V	---	---	1	V
I <sub>S</sub>	Diode Forward Current    *C	T <sub>A</sub> =25°C	---	---	2.8	A
Switching						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =6V, I <sub>D</sub> =6.5A	---	8.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.5	---	nC
Q <sub>gd</sub>	Gate-Drain Charge		---	2.2	---	nC
t <sub>d ( on )</sub>	Turn-on Delay Time	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, R <sub>L</sub> =1.5    , R <sub>GEN</sub> =3	---	8	---	ns
t <sub>r</sub>	Turn-on Rise Time		---	5	---	ns
t <sub>d( off )</sub>	Turn-off Delay Time		---	14	---	ns
t <sub>f</sub>	Turn-Off Fall Time		---	12	---	ns
Dynamic						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> = 6V, f=1MHz	---	850	---	pF
C <sub>oss</sub>	Output Capacitance		---	180	---	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		---	95	---	pF

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .

The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating, package limited 8A.

D: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycles  $\leq 2\%$ .

## Typical Characteristics

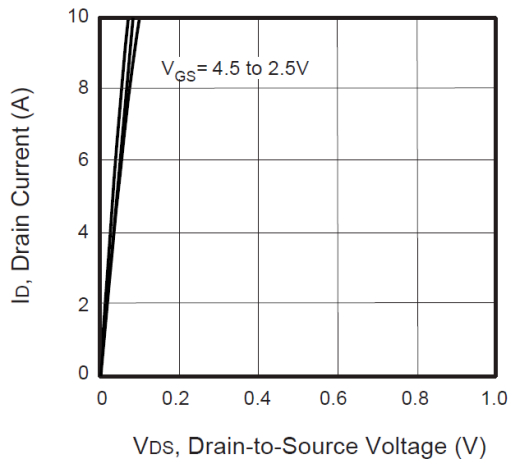


Figure 1. Output Characteristics

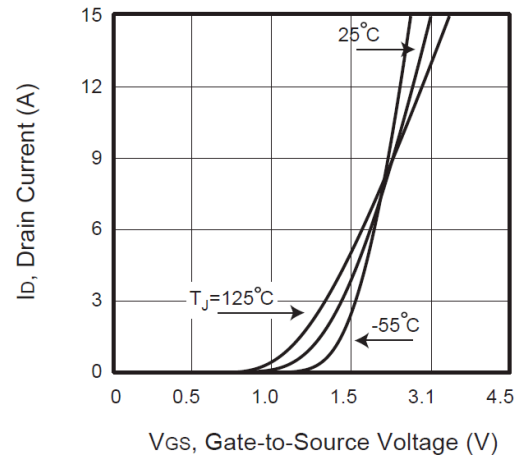


Figure 2. Transfer Characteristics

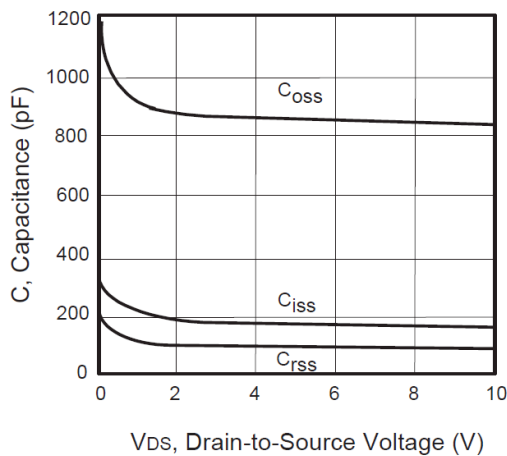


Figure 3. Capacitance

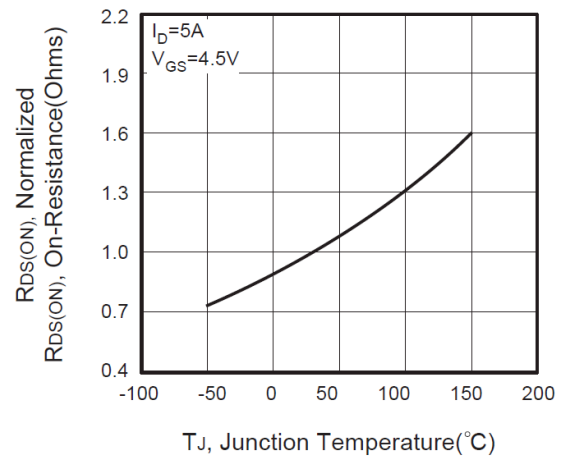


Figure 4. On-Resistance Variation with Temperature

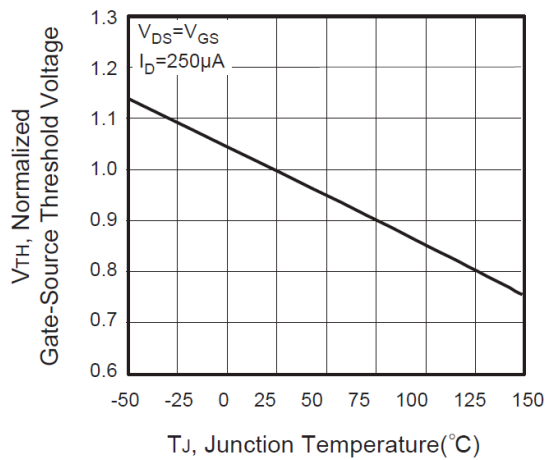


Figure 5. Gate Threshold Variation with Temperature

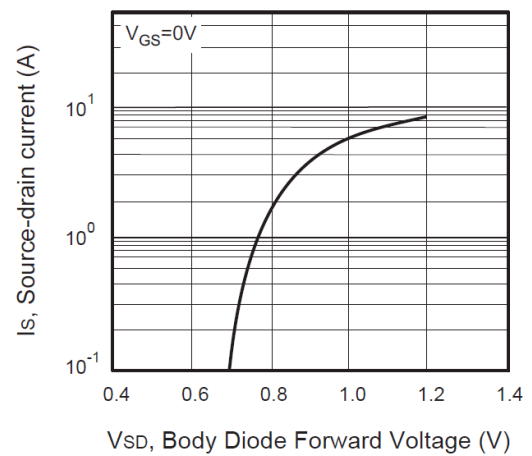
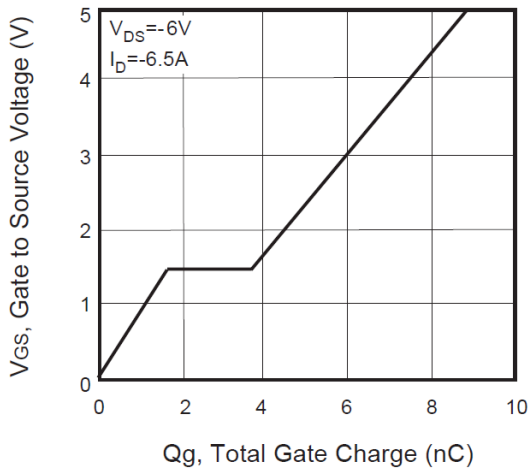
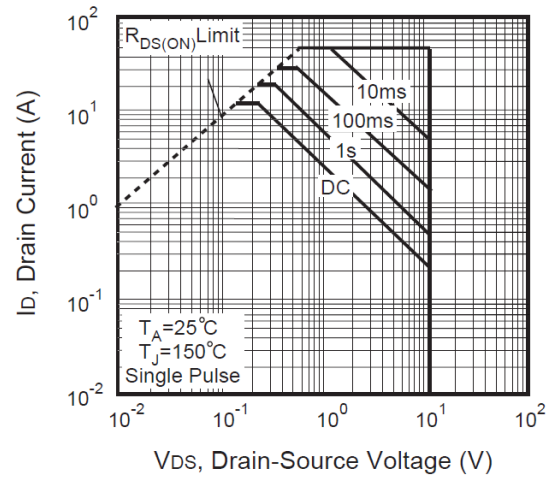


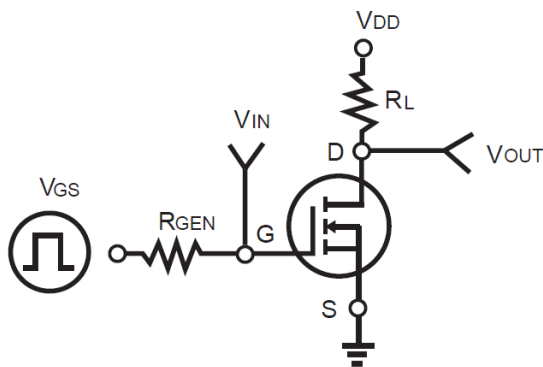
Figure 6. Body Diode Forward Voltage Variation with Source Current



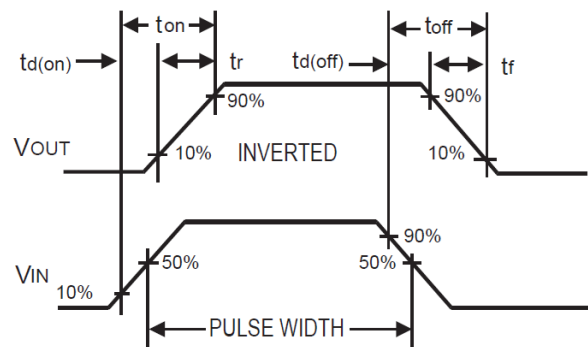
**Figure 7. Gate Charge**



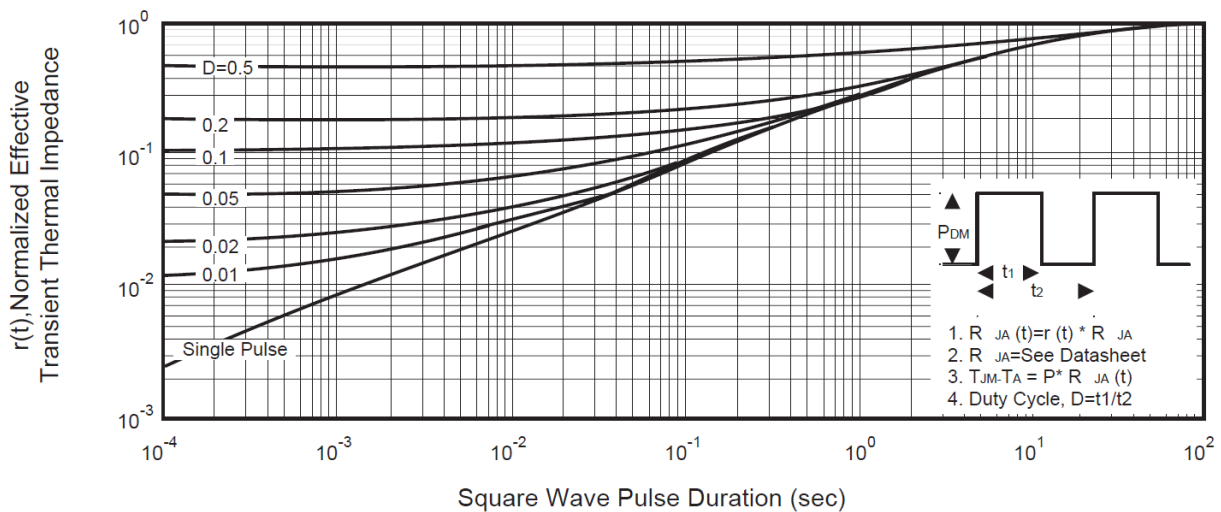
**Figure 8. Maximum Safe Operating Area**



**Figure 9. Switching Test Circuit**

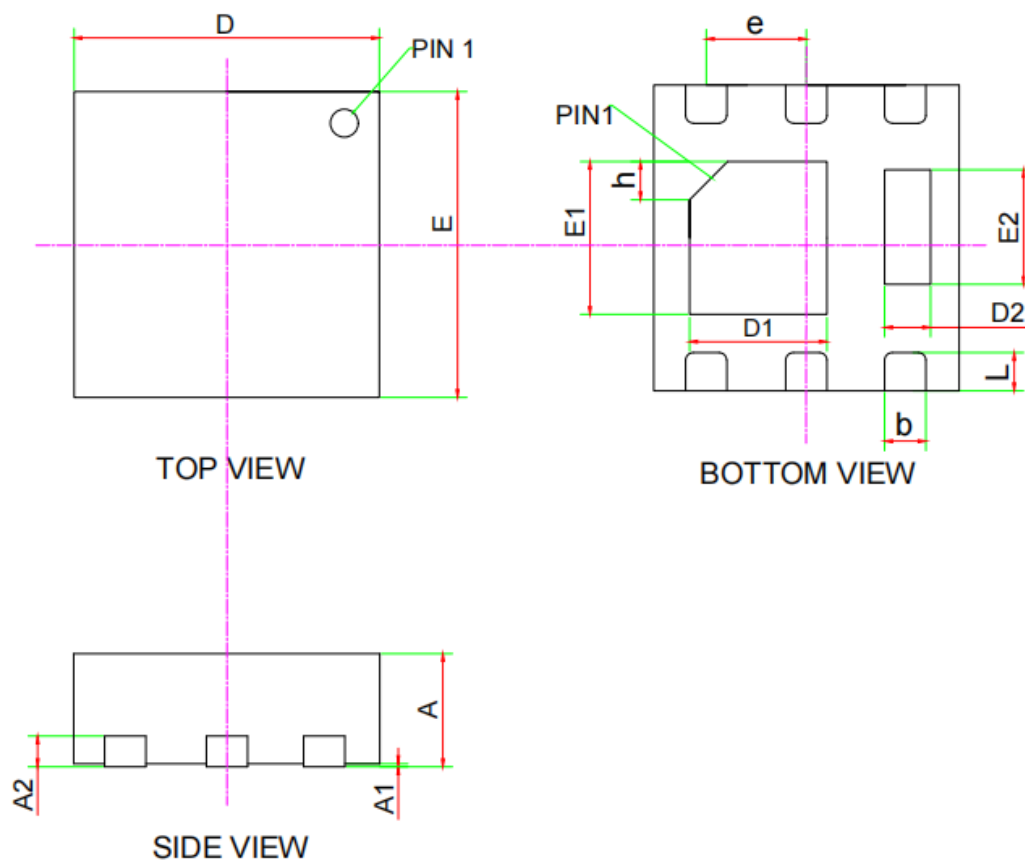


**Figure 10. Switching Waveforms**



**Figure 11. Normalized Thermal Transient Impedance Curve**

## Packaging information



SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.18	0.20	0.25
b	0.20	0.27	0.34
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
e	0.65 BSC		



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